



# BAV101 ~ BAV103

## SMALL SIGNAL SWITCHING DIODE

### FEATURES

- Silicon epitaxial planar diode
- Fast switching diodes
- 300mw power dissipation
- High temperature soldering guaranteed  
250°C/10S at terminals

### MECHANICAL DATA

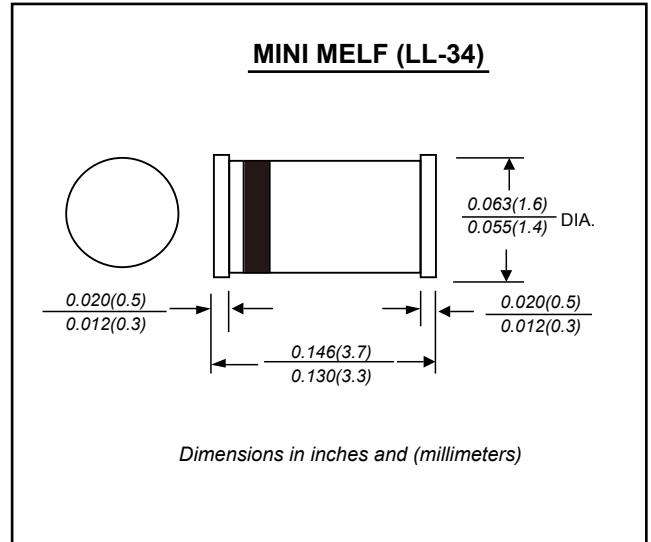
**Case:** MINI MELF glass sealed envelope.

**Terminals:** Plated axial leads, solderable per MIL-STD-750, Method 2026

**Polarity:** Color band denotes cathode end

**Mounting Position:** Any

**Weight:** 0.002 ounce, 0.05 grams



### Maximum Ratings ( $T_A=25^\circ\text{C}$ Unless otherwise noted)

PARAMETER	SYMBOL	BAV101	BAV102	BAV103	UNITS
Reverse Voltage	$V_R$	100	150	200	V
Peak Reverse Voltage	$V_{RRM}$	120	200	250	V
Rectified Current (Average), Half Wave Rectification with Resistive Load and $f \geq 50$ Hz	$I_O$	200			mA
Peak Forward Surge Current, $t=1000\text{ms}$	$I_{FSM}$	1.0			A
Power Dissipation Derate Above at $25^\circ\text{C}$	$P_D$	300			mW
Maximum Forward Voltage, $I_F = 100\text{mA}$	$V_F$	1.0			V
Maximum DC Reverse Current at Rated DC Blocking Voltage $T_J = 25^\circ\text{C}$	$I_R$	0.1			$\mu\text{A}$
Typical Junction Capacitance( Note 1)	$C_J$	3.0			pF
Maximum Reverse Recovery (Note 2)	$t_{rr}$	75			ns
Typical Thermal Resistance	$R_{\theta JA}$	350			$^\circ\text{C} / \text{W}$
Operation Junction Storage Temperature Range	$T_{STG}$	-65 to +175			$^\circ\text{C}$

NOTE:

1.  $C_J$  at  $V_R=0$ ,  $f=1\text{MHz}$

2. From  $I_F=10\text{mA}$  to  $I_R=-1\text{mA}$ ,  $V_R=6\text{Volts}$ ,  $R_L=100\Omega$



# BAV101 ~ BAV103

## RATINGS AND CHARACTERISTIC CURVES

